74AUP2G98

Low-power dual PCB configurable multiple function gate

Rev. 1 — 4 November 2014 Product data sheet

1. General description

The 74AUP2G98 is a dual configurable multiple function gate with Schmitt-trigger inputs. Each gate within the device can be configured as any of the following logic functions MUX, AND, OR, NAND, NOR, inverter and buffer; using the 3-bit input. All inputs can be connected directly to V_{CC} or GND.

This device ensures very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the potentially damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
  - HBM JESD22-A114F exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation
- Multiple package options
- Specified from −40 °C to +85 °C and −40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G98DP	−40 °C to +85 °C	TSSOP10	plastic thin shrink small outline package; 10 leads; body width 3 mm	SOT552-1
74AUP2G98GM	−40 °C to +125 °C	XQFN10	plastic extremely thin quad flat package; no leads; 10 terminals; body 2 × 1.55 × 0.5 mm	SOT1049-3
74AUP2G98GU	−40 °C to +125 °C	XQFN10	plastic, extremely thin quad flat package; no leads; 10 terminals; body 1.40 × 1.80 × 0.50 mm	SOT1160-1
74AUP2G98GF	−40 °C to +125 °C	XSON10	plastic extremely thin small outline package; no leads; 10 terminals; body 1.0 × 1.7 × 0.5 mm	SOT1081-2

4. Marking

Table 2. Marking

Type number	Marking code[1]
74AUP2G98DP	a9
74AUP2G98GM	a9
74AUP2G98GU	a9
74AUP2G98GF	a9

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

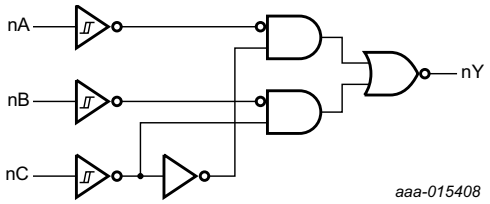


Fig 1. Logic diagram (one gate)

6. Pinning information

6.1 Pinning

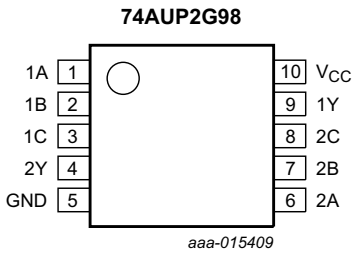


Fig 2. Pin configuration SOT552-1 (TSSOP10)

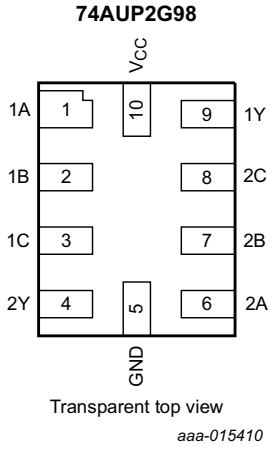


Fig 3. Pin configuration SOT1049-3 (XQFN10)

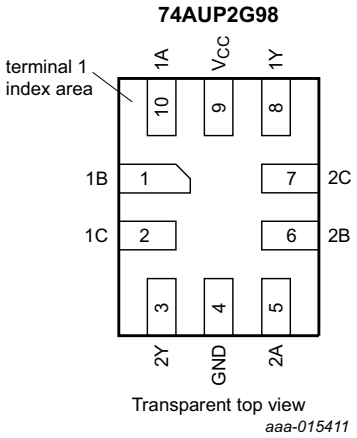


Fig 4. Pin configuration SOT1160-1 (XQFN10)

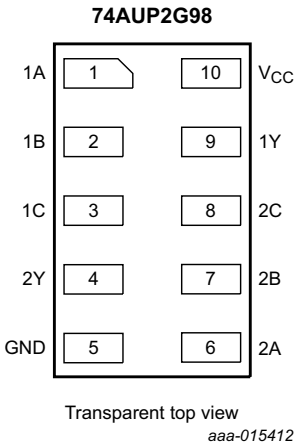


Fig 5. Pin configuration SOT1081-2 (XSON10)

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT552-1, SOT1049-3 and SOT1081-2	SOT1160-1	
1A, 2A	1, 6	10, 5	data input
1B, 2B	2, 7	1, 6	data input
1C, 2C	3, 8	2, 7	data input
1Y, 2Y	9, 4	8, 3	data output
GND	5	4	ground (0 V)
V_{CC}	10	9	supply voltage

7. Functional description

Table 4. Function table[1]

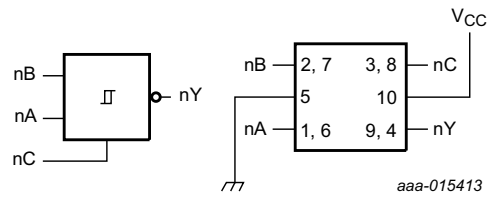
Input			Output
nC	nB	nA	nY
L	L	L	H
L	L	H	H
L	H	L	L
L	H	H	L
H	L	L	H
H	L	H	L
H	H	L	H
H	H	H	L

[1] H = HIGH voltage level; L = LOW voltage level.

7.1 Logic configurations

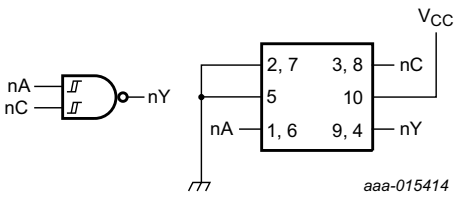
Table 5. Function selection table

Logic function	Figure
2-input MUX with inverted output	see Figure 6
2-input NAND	see Figure 7
2-input NOR with one input inverted	see Figure 8
2-input AND with one input inverted	see Figure 8
2-input NAND with one input inverted	see Figure 9
2-input OR with one input inverted	see Figure 9
2-input NOR	see Figure 10
Buffer	see Figure 11
Inverter	see Figure 12



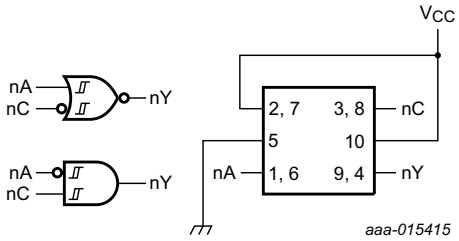
Pin numbers are not valid for SOT1160-1 package

Fig 6. 2-input MUX with inverted output



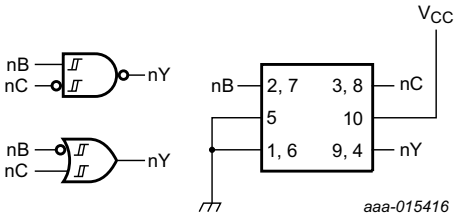
Pin numbers are not valid for SOT1160-1 package

Fig 7. 2-input NAND gate



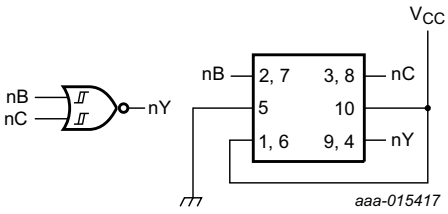
Pin numbers are not valid for SOT1160-1 package

Fig 8. 2-input AND gate with input A inverted or 2-input NOR gate with inverted C input



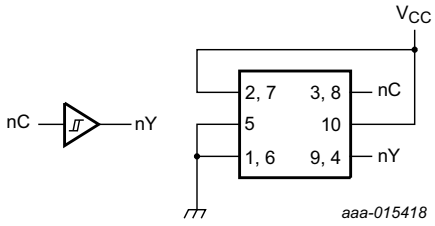
Pin numbers are not valid for SOT1160-1 package

Fig 9. 2-input OR gate with input B inverted or 2-input NAND gate with input C inverted



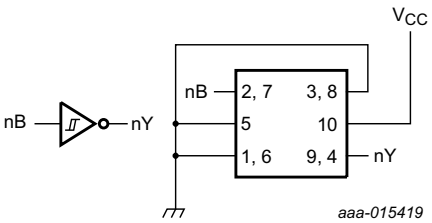
Pin numbers are not valid for SOT1160-1 package

Fig 10. 2-input NOR gate



Pin numbers are not valid for SOT1160-1 package

Fig 11. Buffer



Pin numbers are not valid for SOT1160-1 package

Fig 12. Inverter

8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		−0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	−50	-	mA
V_I	input voltage	[1]	−0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0$ V	−50	-	mA
V_O	output voltage	Active mode and Power-down mode [1]	−0.5	+4.6	V
I_O	output current	V_O = 0 V to V_{CC}	-	±20	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		−50	-	mA
T_{stg}	storage temperature		−65	+150	°C
P_{tot}	total power dissipation	T_{amb} = −40 °C to +125 °C [2]	-	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP10 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
For XQFN10 (SOT1049-3) package: above 132 °C the value of P_{tot} derates linearly with 14.1 mW/K.
For XQFN10 (SOT1160-1) package: above 128 °C the value of P_{tot} derates linearly with 11.5 mW/K.
For XSON10 package: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 7. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; V_{CC} = 0 V	0	3.6	V
T_{amb}	ambient temperature		−40	+125	°C

10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = −20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.1	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.75 × V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	1.11	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.32	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.9	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.72	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.6	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	0.3 × V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.31	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.31	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.31	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.44	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.31	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.44	V
I_I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	-	-	±0.2	μA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.5	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC}$ − 0.6 V; I_O = 0 A; V_{CC} = 3.3 V [1]	-	-	40	μA
C_I	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}	-	1.1	-	pF
C_O	output capacitance	V_O = GND; V_{CC} = 0 V	-	1.7	-	pF

Table 8. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = −40 °C to +85 °C						
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = −20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.1	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.7 × V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	1.03	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.30	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	1.97	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.85	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.67	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.55	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	0.3 × V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.37	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.33	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V
I_I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.5	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	-	-	±0.6	μA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC}$ − 0.6 V; I_O = 0 A; V_{CC} = 3.3 V [1]	-	-	50	μA

Table 8. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = −40 °C to +125 °C						
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = −20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.11	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.6 × V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	0.93	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.17	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.67	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.30	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	0.33 × V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.41	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.39	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.36	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.50	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.36	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.50	V
I_I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.75	μA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	-	-	±0.75	μA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μA
ΔI_{CC}	additional supply current	V_I = V_{CC} − 0.6 V; I_O = 0 A; V_{CC} = 3.3 V [1]	-	-	75	μA

[1] One input at V_{CC} − 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 14.

Symbol	Parameter	Conditions	T_{amb} = 25 °C			T_{amb} = –40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 5 pF									
t_{pd}	propagation delay	nA, nB, nC to nY; see Figure 13 [2]							
		V_{CC} = 0.8 V	-	23.3	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	2.9	6.7	12.9	2.7	13.2	13.4	ns
		V_{CC} = 1.4 V to 1.6 V	2.4	4.8	7.7	2.4	8.3	8.7	ns
		V_{CC} = 1.65 V to 1.95 V	2.2	4.0	6.3	1.9	7.0	7.4	ns
		V_{CC} = 2.3 V to 2.7 V	2.0	3.2	4.6	1.8	5.2	5.4	ns
		V_{CC} = 3.0 V to 3.6 V	1.9	2.9	4.0	1.6	4.2	4.4	ns
C_L = 10 pF									
t_{pd}	propagation delay	nA, nB, nC to nY; see Figure 13 [2]							
		V_{CC} = 0.8 V	-	27.1	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	3.3	7.6	14.5	3.0	15.1	15.3	ns
		V_{CC} = 1.4 V to 1.6 V	2.7	5.4	8.8	2.8	9.5	9.9	ns
		V_{CC} = 1.65 V to 1.95 V	2.5	4.6	7.2	2.3	8.0	8.4	ns
		V_{CC} = 2.3 V to 2.7 V	2.4	3.8	5.3	2.2	5.9	6.2	ns
		V_{CC} = 3.0 V to 3.6 V	2.3	3.5	4.7	2.0	4.9	5.2	ns
C_L = 15 pF									
t_{pd}	propagation delay	nA, nB, nC to nY; see Figure 13 [2]							
		V_{CC} = 0.8 V	-	30.6	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	3.6	8.4	16.1	3.3	16.9	17.2	ns
		V_{CC} = 1.4 V to 1.6 V	3.0	6.0	9.7	3.1	10.5	11.0	ns
		V_{CC} = 1.65 V to 1.95 V	2.8	5.1	7.9	2.5	8.9	9.3	ns
		V_{CC} = 2.3 V to 2.7 V	2.7	4.2	5.9	2.5	6.6	7.0	ns
		V_{CC} = 3.0 V to 3.6 V	2.5	3.9	5.2	2.2	5.5	5.8	ns
C_L = 30 pF									
t_{pd}	propagation delay	nA, nB, nC to nY; see Figure 13 [2]							
		V_{CC} = 0.8 V	-	38.7	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	4.5	10.7	21.1	4.1	22.0	22.4	ns
		V_{CC} = 1.4 V to 1.6 V	3.8	7.6	12.3	3.8	13.5	14.2	ns
		V_{CC} = 1.65 V to 1.95 V	3.5	6.3	10.1	3.1	11.3	11.9	ns
		V_{CC} = 2.3 V to 2.7 V	3.4	5.3	7.5	3.2	8.4	8.9	ns
		V_{CC} = 3.0 V to 3.6 V	3.2	5.0	6.7	2.9	7.1	7.5	ns

Table 9. Dynamic characteristics *…continued*

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 14.

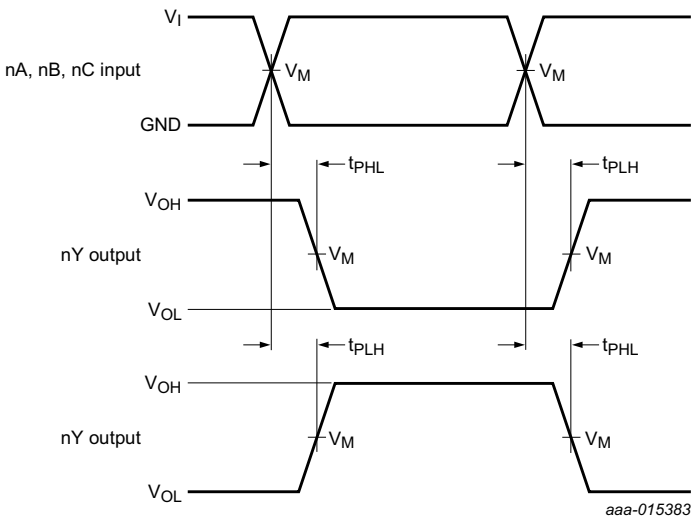
Symbol	Parameter	Conditions	T_{amb} = 25 °C			T_{amb} = –40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 5 pF, 10 pF, 15 pF and 30 pF									
C_{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC} [3]							
		V_{CC} = 0.8 V	-	2.7	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V	-	2.9	-	-	-	-	pF
		V_{CC} = 1.4 V to 1.6 V	-	3.0	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V	-	3.2	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	3.8	-	-	-	-	pF
		V_{CC} = 3.0 V to 3.6 V	-	4.4	-	-	-	-	pF

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



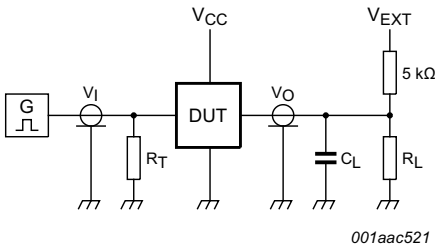
Measurement points are given in Table 10.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 13. Input nA, nB and nC to output nY propagation delay times.

Table 10. Measurement points

Supply voltage	Output	Input		
V_{CC}	V_M	V_M	V_I	$t_r = t_f$
0.8 V to 3.6 V	$0.5V_{CC}$	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	≤ 3.0 ns



Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 14. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L[1]	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2V_{CC}$

[1] For measuring enable and disable times, R_L = 5 kΩ, for measuring propagation delays, setup and hold times and pulse width R_L = 1 MΩ.

13. Transfer characteristics

Table 12. Transfer characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit, see Figure 14.

Symbol	Parameter	Conditions	T_{amb} = 25 °C			T_{amb} = –40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V_{T+}	positive-going threshold voltage	see Figure 15 and Figure 16							
		V_{CC} = 0.8 V	0.30	-	0.60	0.30	0.60	0.62	V
		V_{CC} = 1.1 V	0.53	-	0.90	0.53	0.90	0.92	V
		V_{CC} = 1.4 V	0.74	-	1.11	0.74	1.11	1.13	V
		V_{CC} = 1.65 V	0.91	-	1.29	0.91	1.29	1.31	V
		V_{CC} = 2.3 V	1.37	-	1.77	1.37	1.77	1.80	V
		V_{CC} = 3.0 V	1.88	-	2.29	1.88	2.29	2.32	V
V_{T-}	negative-going threshold voltage	see Figure 15 and Figure 16							
		V_{CC} = 0.8 V	0.10	-	0.60	0.10	0.60	0.60	V
		V_{CC} = 1.1 V	0.26	-	0.65	0.26	0.65	0.65	V
		V_{CC} = 1.4 V	0.39	-	0.75	0.39	0.75	0.75	V
		V_{CC} = 1.65 V	0.47	-	0.84	0.47	0.84	0.84	V
		V_{CC} = 2.3 V	0.69	-	1.04	0.69	1.04	1.04	V
		V_{CC} = 3.0 V	0.88	-	1.24	0.88	1.24	1.24	V
V_H	hysteresis voltage	($V_{T+} - V_{T-}$); see Figure 15, Figure 16, Figure 17 and Figure 18							
		V_{CC} = 0.8 V	0.07	-	0.50	0.07	0.50	0.50	V
		V_{CC} = 1.1 V	0.08	-	0.46	0.08	0.46	0.46	V
		V_{CC} = 1.4 V	0.18	-	0.56	0.18	0.56	0.56	V
		V_{CC} = 1.65 V	0.27	-	0.66	0.27	0.66	0.66	V
		V_{CC} = 2.3 V	0.53	-	0.92	0.53	0.92	0.92	V
		V_{CC} = 3.0 V	0.79	-	1.31	0.79	1.31	1.31	V

14. Waveforms transfer characteristics

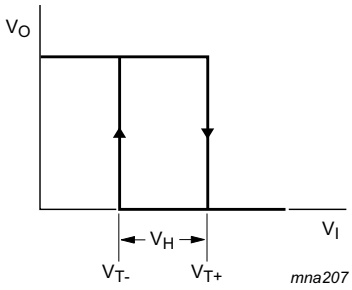
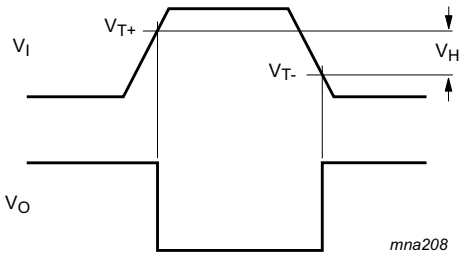


Fig 15. Transfer characteristic



V_{T+} and V_{T-} limits at 70 % and 20 %.

Fig 16. Definition of V_{T+}, V_{T-} and V_H

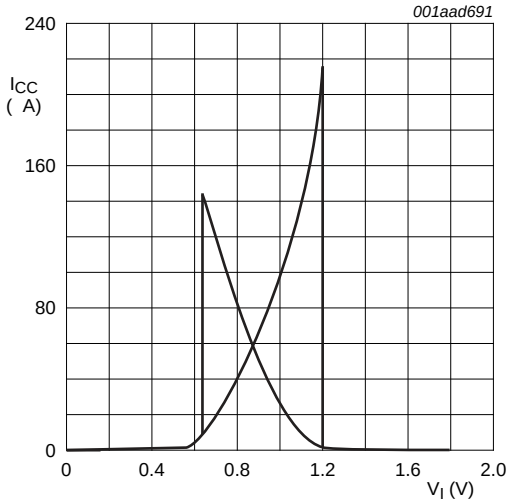


Fig 17. Typical transfer characteristics; V_{CC} = 1.8 V

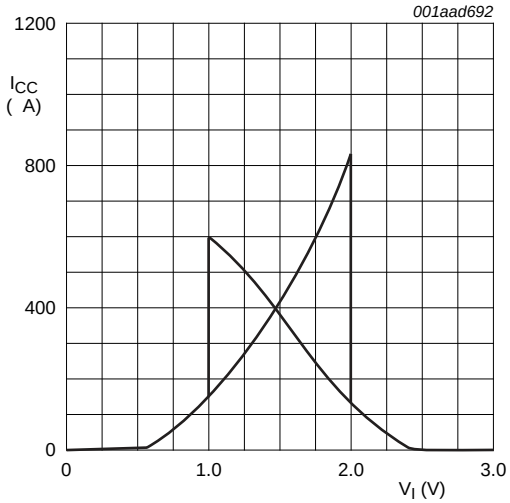
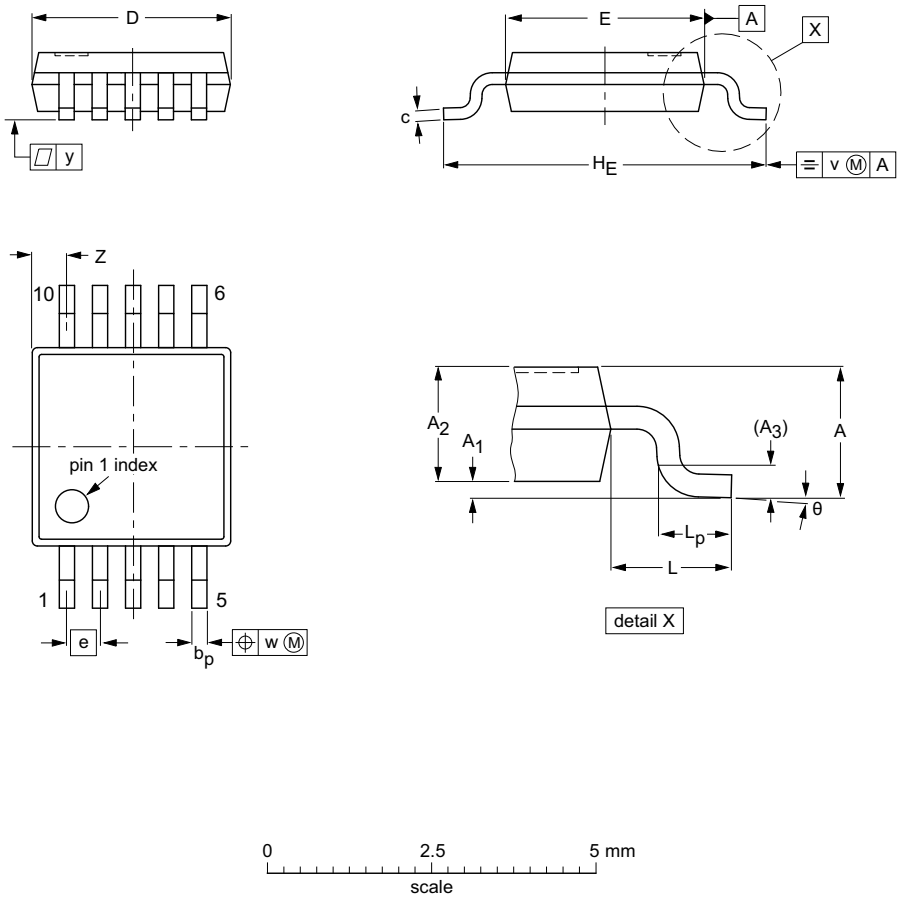


Fig 18. Typical transfer characteristics; V_{CC} = 3.0 V

15. Package outline

TSSOP10: plastic thin shrink small outline package; 10 leads; body width 3 mm **SOT552-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.15	0.23 0.15	3.1 2.9	3.1 2.9	0.5	5.0 4.8	0.95	0.7 0.4	0.1	0.1	0.1	0.67 0.34	6° 0°

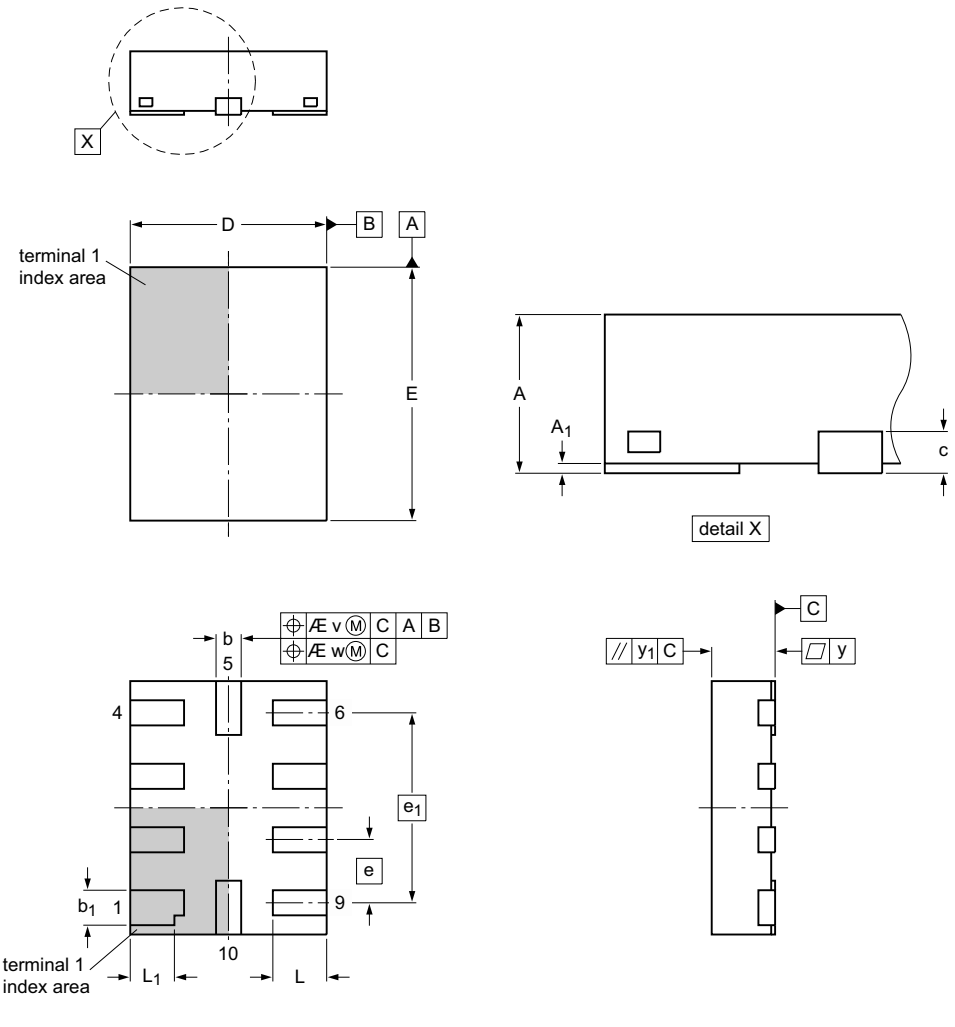
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT552-1						~~99-07-29~~ 03-02-18

Fig 19. Package outline SOT552-1 (TSSOP10)

XQFN10: plastic, extremely thin quad flat package; no leads; 10 terminals; body 1.55 x 2.00 x 0.50 mm **SOT1049-3**



Dimensions

Unit[1]		A	A_1	b	b_1	c	D	E	e	e_1	L	L_1	v	w	y	y_1
mm	max	0.5	0.05	0.25	0.33		1.65	2.1			0.48	0.40				
	nom			0.20	0.28	0.127	1.55	2.0	0.5	1.5	0.43	0.35	0.1	0.05	0.05	0.05
	min		0.00	0.15	0.23		1.45	1.9			0.38	0.30				

Note

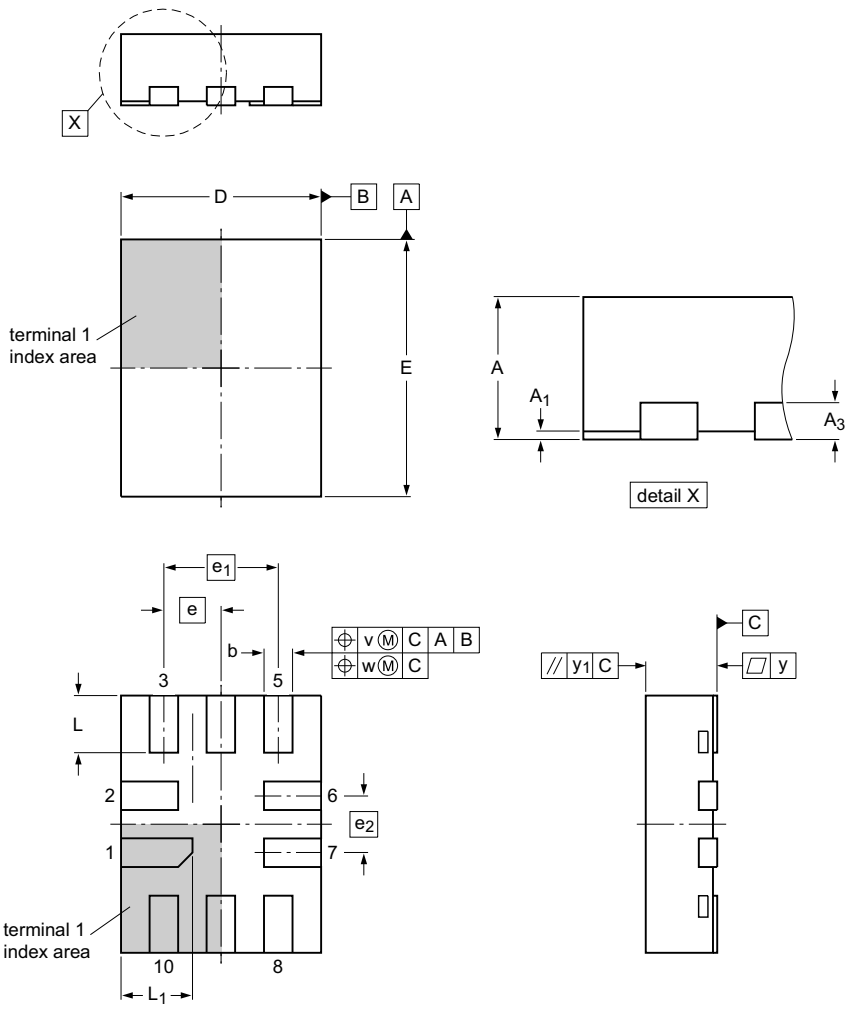
1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

sot1049-3_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1049-3	- - -	MO255	- - -			~~10-12-06~~ 11-03-30

Fig 20. Package outline SOT1049-3 (XQFN10)

XQFN10: plastic, extremely thin quad flat package; no leads; 10 terminals; body 1.40 x 1.80 x 0.50 mm **SOT1160-1**



Dimensions

Unit(1)		A	A_1	A_3	b	D	E	e	e_1	e_2	L	L_1	v	w	y	y_1
mm	max	0.5	0.05		0.25	1.5	1.9				0.45	0.55				
	nom			0.127	0.20	1.4	1.8	0.4	0.8	0.4	0.40	0.50	0.1	0.05	0.05	0.05
	min		0.00		0.15	1.3	1.7				0.35	0.45				

Note

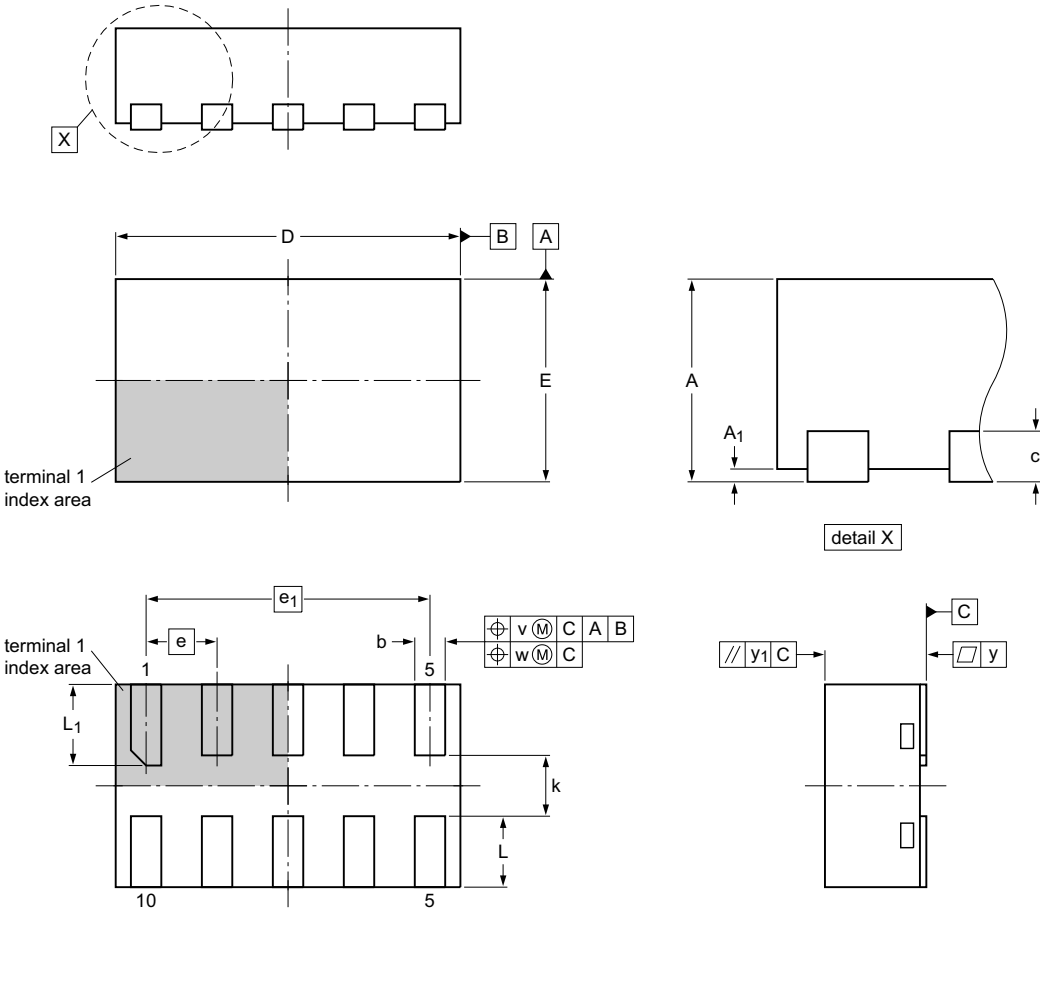
1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

sot1160-1_po

Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOT1160-1	---	---	---		~~09-12-28~~ 09-12-29

Fig 21. Package outline SOT1160-1 (XQFN10)

XSON10: plastic extremely thin small outline package; no leads; 10 terminals; body 1.0 x 1.7 x 0.5 mm **SOT1081-2**



Dimensions

Unit[1]		A	A_1	b	c	D	E	e	e_1	k	L	L_1	v	w	y	y_1
mm	max	0.5	0.05	0.20		1.8	1.1				0.40	0.45				
	nom			0.15	0.127	1.7	1.0	0.35	1.4		0.35	0.40	0.1	0.05	0.05	0.05
	min		0.00	0.10		1.6	0.9			0.2	0.30	0.35				

Note
1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

sot1081-2_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1081-2	- - -	- - -	- - -			~~10-11-08~~ 11-03-30

Fig 22. Package outline SOT1081-2 (XSON10)

16. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
PCB	Printed-Circuit Board

17. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G98 v.1	20141104	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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20. Contents

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